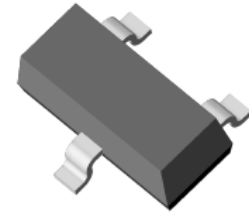


Small Signal Fast Switching Diode

General Description

Dual general-purpose switching diodes, fabricated in planar technology, and packaged in small SOT-23 surface mounted device (SMD) packages.



SOT-23



Features and Benefits

- Silicon epitaxial planar diode
- High switching speed: $tr \leq 4ns$
- Low forward drop voltage and low leakage current
- “Green” device and RoHS compliant device
- Available in full lead (Pb)-free device

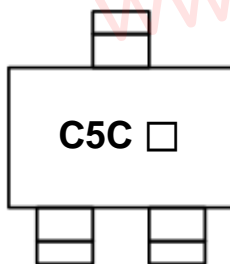
Applications

- Ultra high speed switching application

Ordering Information

Part Number	Marking Code	Package	Packaging
SDS7000	C5C □	SOT-23	Tape & Reel

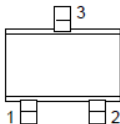
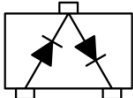
Marking Information



C5C = Specific Device Code

□ = Year & Week Code Marking

Pinning Information

Pin	Description	Simplified Outline	Graphic Symbol
1	Anode (Diode 1)		
2	Cathode (Diode 2)		
3	Cathode (Diode 1), Anode (Diode 2)		

Absolute Maximum Ratings (T_{amb}=25°C, Unless otherwise specified)

Characteristic	Symbol	Ratings	Unit
Maximum repetitive peak reverse voltage	V _{RM}	85	V
Continuous reverse voltage	V _R	80	V
Maximum average forward rectified current	I _O	100	mA
Forward current (DC)	I _F	100	mA
Maximum repetitive peak forward current	I _{FM}	300	mA
Non-repetitive peak forward surge current(t=10ms)	I _{FSM}	2	A
Power dissipation ¹⁾	P _D	150	mW

¹⁾ Device mounted on FR-4 board with recommended pad layout.

Thermal Characteristics (T_{amb}=25°C, Unless otherwise specified)

Characteristic	Symbol	Ratings	Unit
Thermal resistance, junction to ambient ¹⁾	R _{th(j-a)}	830	°C/W
Operating junction temperature	T _j	150	°C
Storage temperature range	T _{stg}	-55 ~ 150	°C

¹⁾ Device mounted on FR-4 board with recommended pad layout.

Electrical Characteristics (T_{amb}=25°C, Unless otherwise specified)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Forward voltage ²⁾	V _{F(1)}	I _F =1mA	-	0.6	-	V
	V _{F(2)}	I _F =10mA	-	0.7	-	V
	V _{F(3)}	I _F =100mA	-	0.9	1.2	V
Reverse leakage current ³⁾	I _R	V _R =80V	-	-	0.5	uA
Total capacitance	C _T	V _R =0V, f=1MHz	-	2.2	4.0	pF
Reverse recovery time	t _{rr}	I _F =10mA (Fig. 5)	-	1.6	4.0	ns

²⁾ Pulse test: t_p≤380μs, Duty cycle≤2%

³⁾ Pulse test: t_p≤5ms, Duty cycle≤2%

Rating and Characteristic Curves

Fig. 1) Typical Forward Characteristics



Fig. 2) Typical Reverse Characteristics

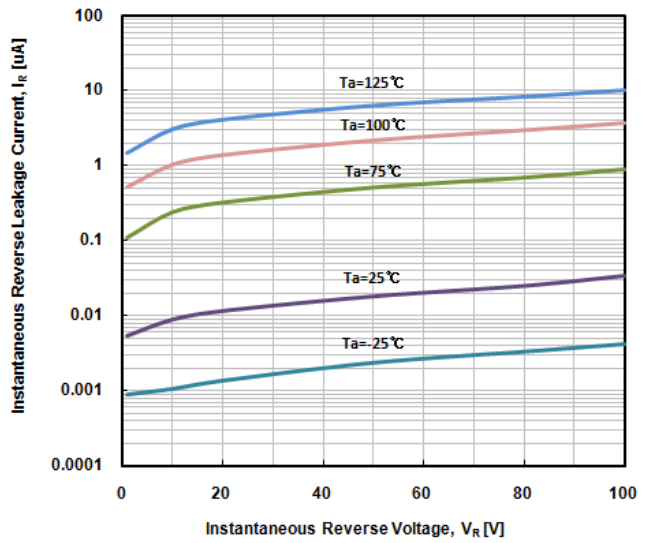


Fig. 3) Typical Total Capacitance Characteristics

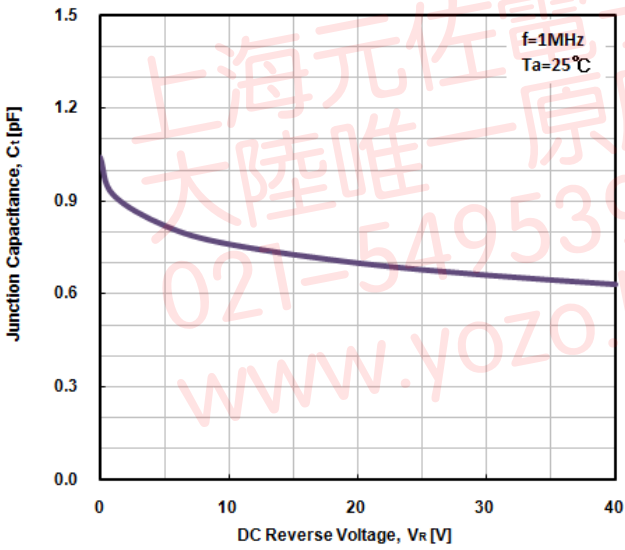


Fig. 4) Reverse Recovery Time vs. Forward Current

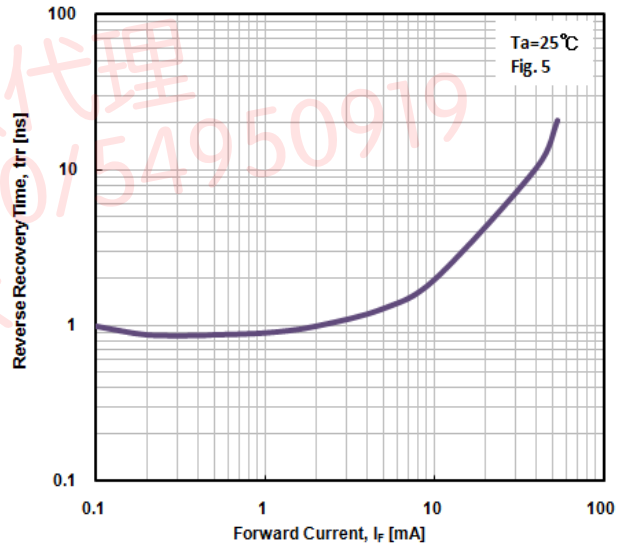
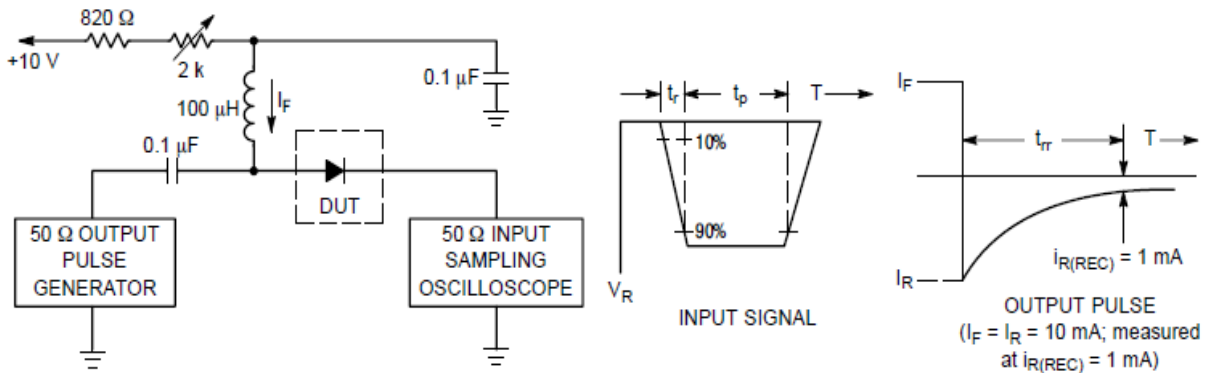
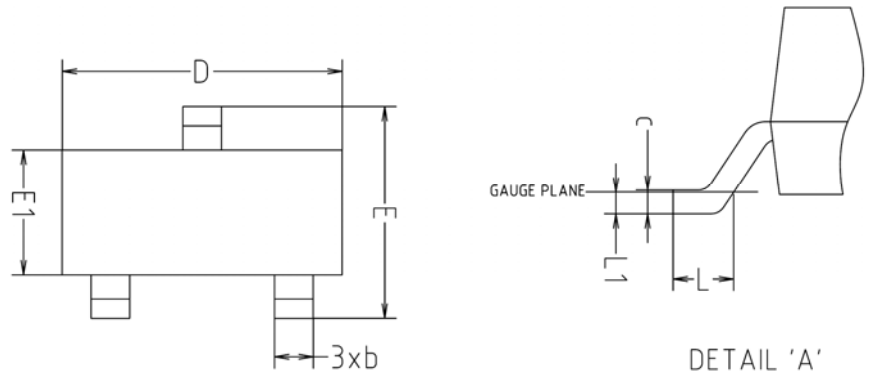


Fig. 5) Reverse recovery time equivalent test circuit



Package Outline Dimensions



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021-54950919
www.yuanzoelectronics.com

SYMBOL	MILLIMETERS			NOTE
	MINIMUM	NOMINAL	MAXIMUM	
A1	0.00	-	0.10	
A2	0.82	-	1.02	
b	0.39	0.42	0.45	
c	0.09	0.12	0.15	
D	2.80	2.90	3.00	
E	2.20	2.40	2.60	
E1	1.20	1.30	1.40	
e	1.90BSC			
L	0.20	-	-	
L1	0.12BSC			

※ Recommend PCB solder land (Unit : mm)

